

N-Channel Power MOSFET

600V, 0.7A, 10Ω

FEATURES

- Pb-free plating
- RoHS compliant
- Halogen-free according to IEC 61249-2-21

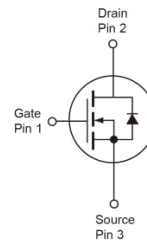
APPLICATIONS

- Lighting
- Charger
- Power Supply
- Switching applications

PRODUCT SUMMARY			
PARAMETER		VALUE	UNIT
V_{DS}		600	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	10	Ω
Q_g	$V_{GS} = 10V$	7.4	nC



SOT-223



Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	600	V	
Gate-Source Voltage		V_{GS}	±30	V	
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	0.7	A	
	$T_C = 100^\circ\text{C}$		0.5		
	$T_A = 25^\circ\text{C}$		0.3		
Pulsed Drain Current ^(Note 1)		I_{DM}	2.8	A	
Total Power Dissipation		$T_C = 25^\circ\text{C}$	P_D	11	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C	

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	11	°C/W
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	60	°C/W

Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2.5	3.1	4.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$	I_{DSS}	--	--	10	μA
Drain-Source On-State Resistance (Note 2)	$V_{GS} = 10\text{V}, I_D = 0.5\text{A}$	$R_{DS(on)}$	--	9.3	10	Ω
Dynamic						
Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 480\text{V}, I_D = 1\text{A}$	Q_g	--	7.4	--	nC
Gate-Source Charge		Q_{gs}	--	1.4	--	
Gate-Drain Charge		Q_{gd}	--	4.7	--	
Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	158	--	pF
Output Capacitance		C_{oss}	--	25	--	
Reverse Transfer Capacitance		C_{rss}	--	1	--	
Switching (Note 3)						
Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 300\text{V}, I_D = 1\text{A}, R_G = 25\Omega$	$t_{d(on)}$	--	6.4	--	ns
Rise Time		t_r	--	10	--	
Turn-Off Delay Time		$t_{d(off)}$	--	14	--	
Fall Time		t_f	--	26	--	
Source-Drain Diode						
Diode Forward Voltage (Note 2)	$V_{GS} = 0\text{V}, I_S = 1\text{A}$	V_{SD}	--	0.8	1.4	V
Source Current	Integral reverse diode In the MOSFET	I_S	--	--	1	A
Source Current (Pulse)		I_{SM}	--	--	4	

Notes:

1. Pulsed width limited by maximum junction temperature.
2. Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Switching time is essentially independent of operating temperature.

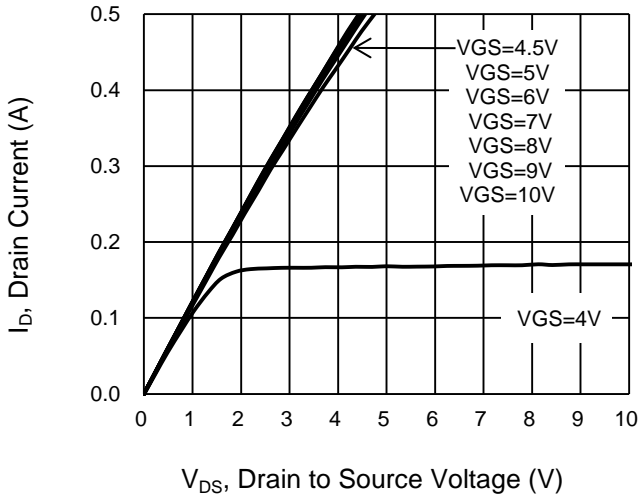
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM1NB60CW RPG	SOT-223	2,500 pcs / 13" Reel

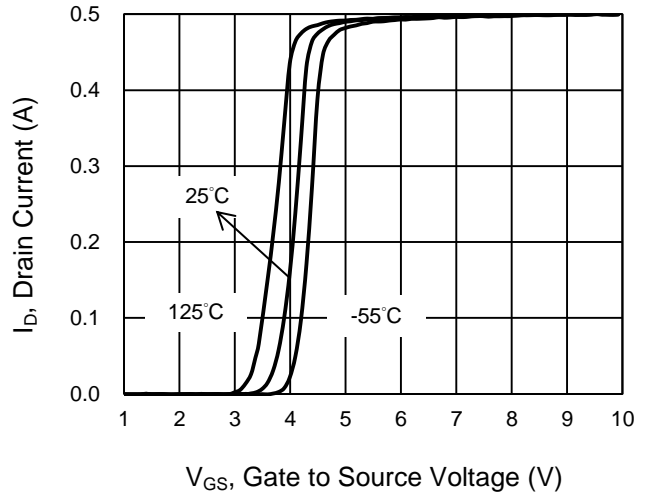
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

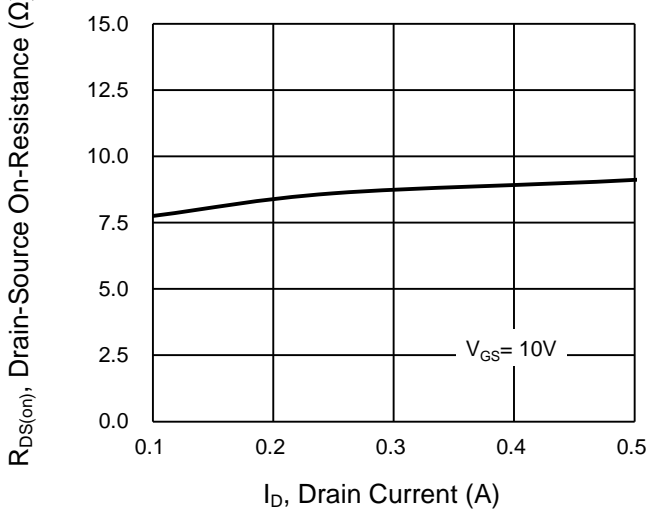
Output Characteristics



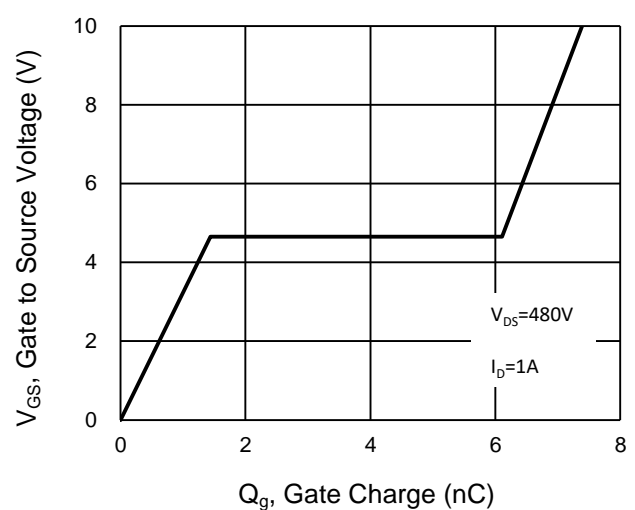
Transfer Characteristics



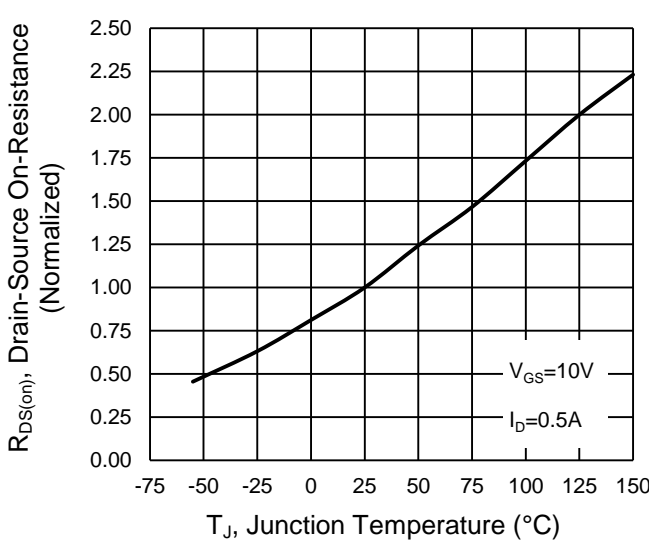
On-Resistance vs. Drain Current



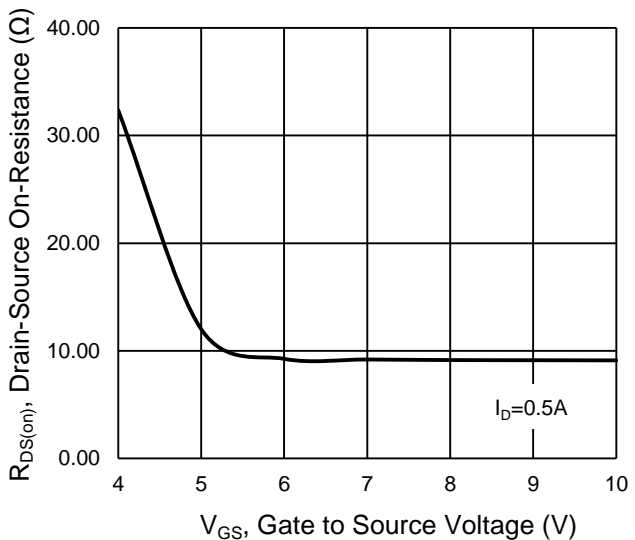
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



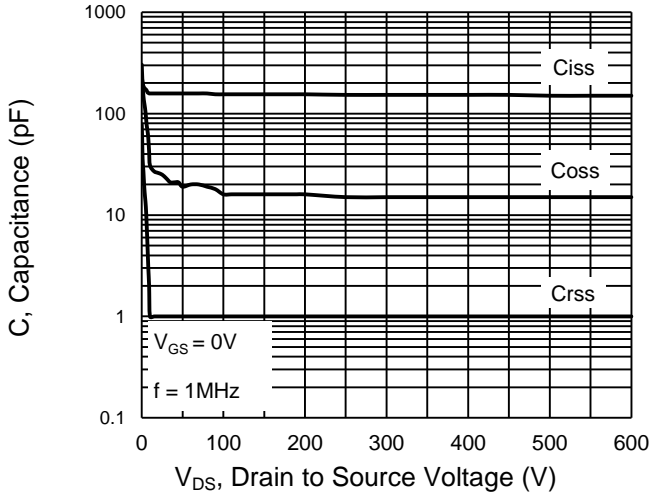
On-Resistance vs. Gate-Source Voltage



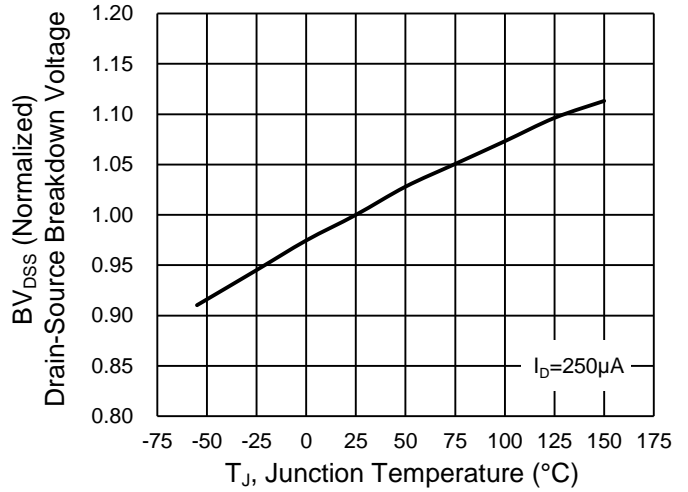
CHARACTERISTICS CURVES

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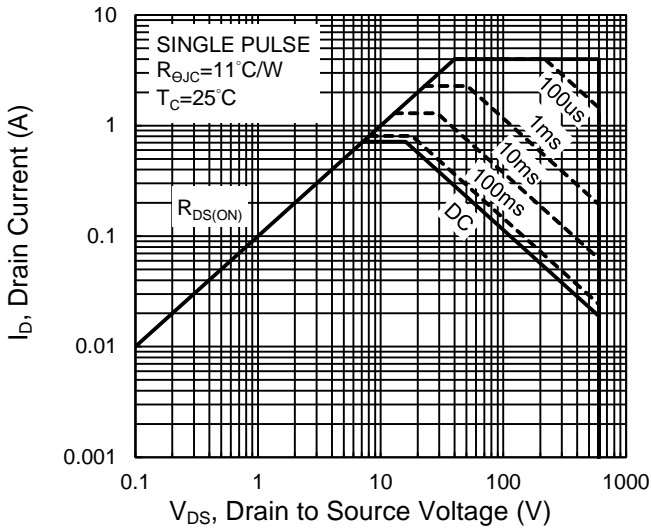
Capacitance vs. Drain-Source Voltage



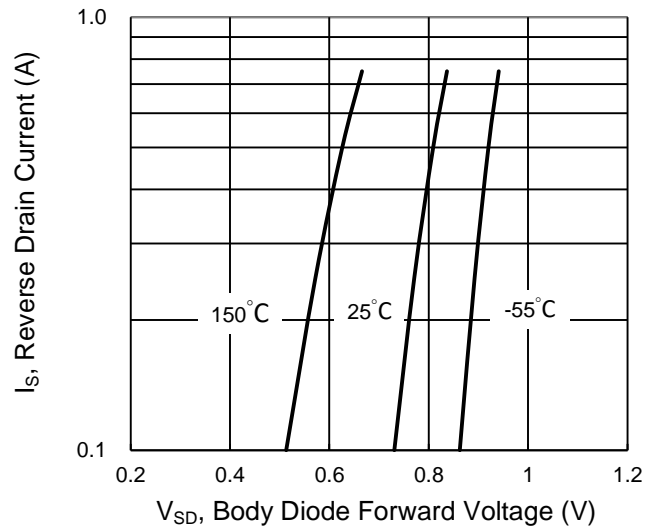
BV_{DSS} vs. Junction Temperature



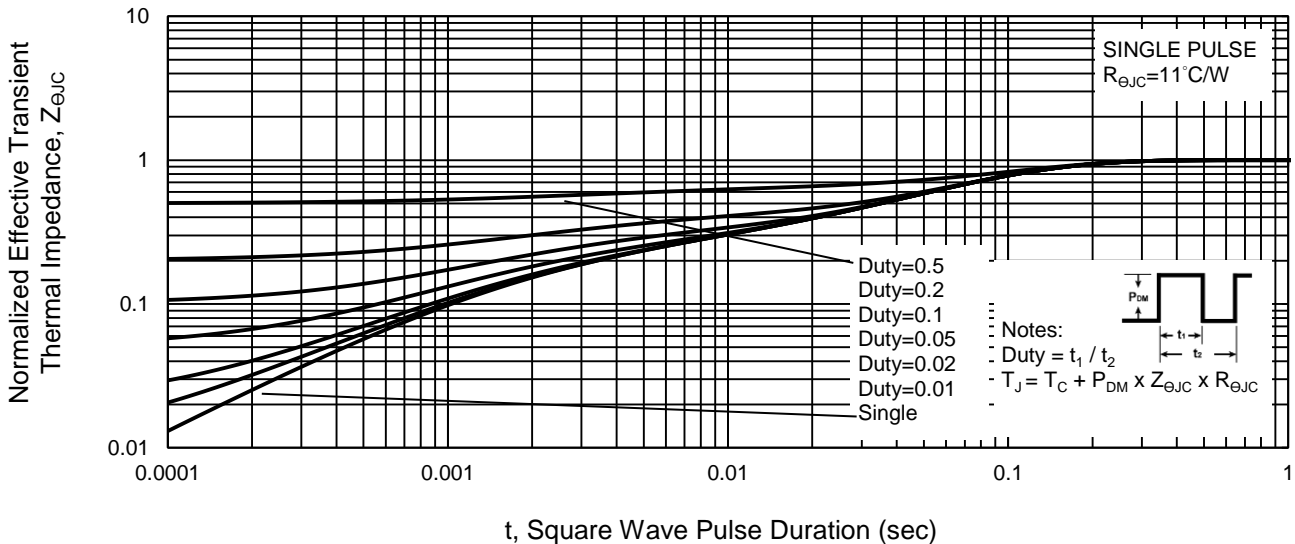
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



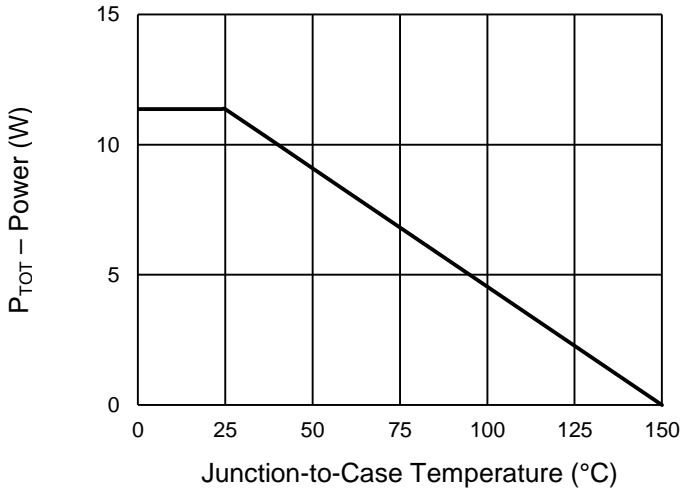
Normalized Thermal Transient Impedance, Junction-to-Case



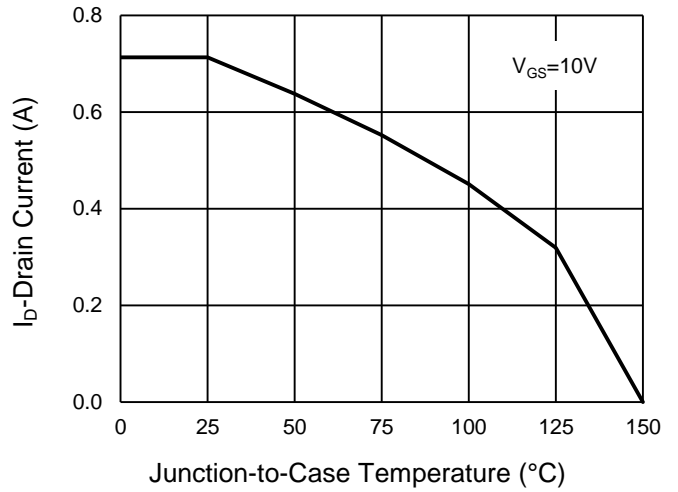
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

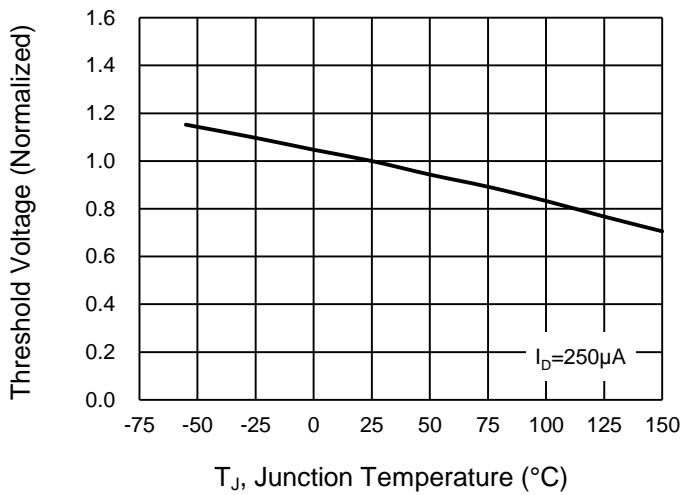
Power Dissipation



Drain Current

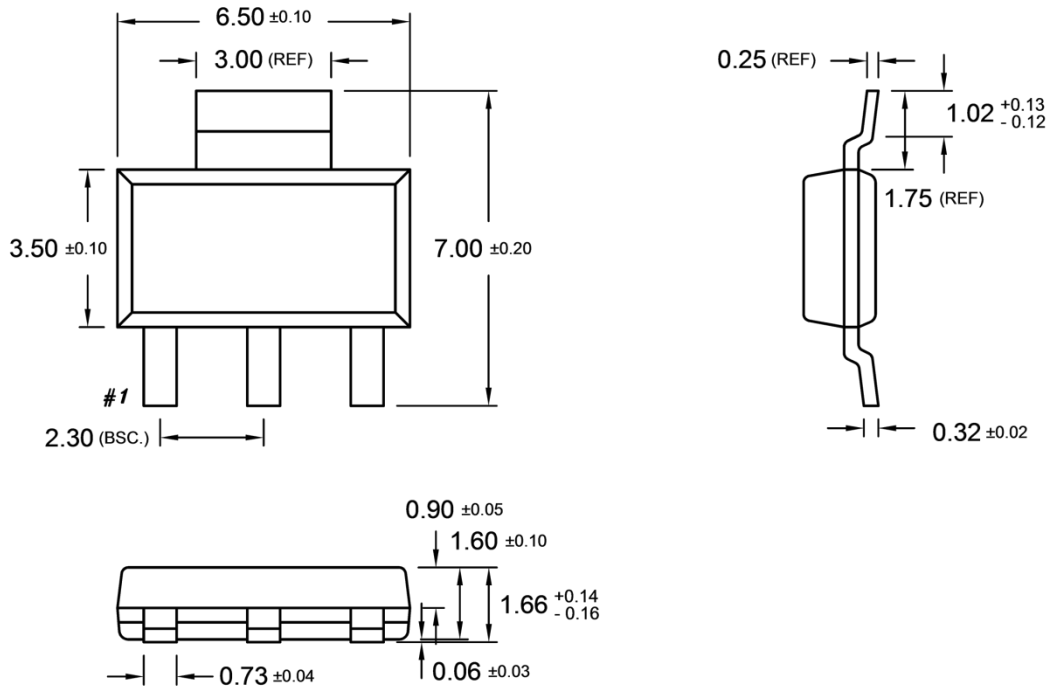


Normalized gate threshold voltage vs Temperature

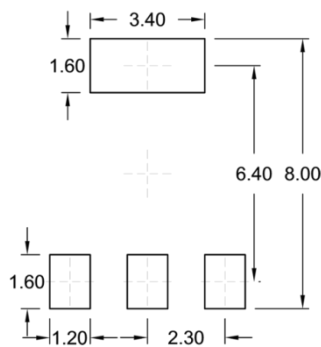


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

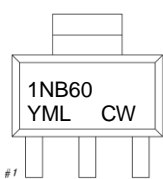
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SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y** = Year Code
- M** = Month Code
- O** =Jan **P** =Feb **Q** =Mar **R** =Apr
- S** =May **T** =Jun **U** =Jul **V** =Aug
- W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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